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## PATENT ABSTRACTS OF JAPAN

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**INOUE MINORU**(54) **SPUTTERING APPARATUS**

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(57) Abstract:

**PURPOSE:** To vertically make sputter particles incident even on the bottom parts of minute holes and to form the wiring layer of uniform film thickness by introducing the sputtering gas concentrically to the erosion area of the surface of a target.

**CONSTITUTION:** The particles discharged from the target 3 in the treatment chamber 1 in which the sputtering gas is introduced are made incident on an object 15 to be treated confronting to the target 3 to deposit the particles on the surface of the object 15 to be treated to form film. In this sputtering apparatus, for example, the introduction opening 11 of sputtering gas is disposed around the target 3, and the sputtering gas is supplied from here to the erosion area 3a. By this method, while the pressure in this area is maintained in such a pressure that sputtering is efficiently carried out, the pressure around the semiconductor base plate 15 mounted on a stage 4 can be held at such a pressure that the sputter particles are easily made incident in the vertical direction.

